Octal 3-State Inverting Buffer/Line Driver/Line Receiver

High-Performance Silicon-Gate CMOS

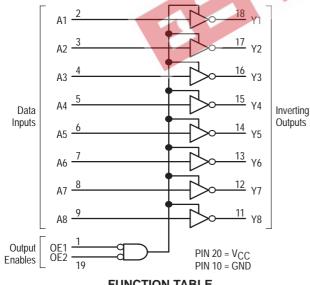
The MC74HC540A is identical in pinout to the LS540. The device inputs are compatible with Standard CMOS outputs. External pullup resistors make them compatible with LSTTL outputs.

The HC540A is an octal inverting buffer/line driver/line receiver designed to be used with 3-state memory address drivers, clock drivers, and other bus-oriented systems. This device features inputs and outputs on opposite sides of the package and two ANDed active-low output enables.

The HC540A is similar in function to the HC541A, which has non-inverting outputs.

- Output Drive Capability: 15 LSTTL Loads
- Outputs Directly Interface to CMOS, NMOS and TTL
- Operating Voltage Range: 2 to 6V
- Low Input Current: 1μA
- High Noise Immunity Characteristic of CMOS Devices
- In Compliance With the JEDEC Standard No. 7A Requirements
- Chip Complexity: 124 FETs or 31 Equivalent Gates

LOGIC DIAGRAM



FUNCTION TABLE

	Inputs	Output V	
OE1	OE2	Α	Output Y
L	L	L	Н
L	L	Н	L
Н	Х	Χ	z
Х	Н	Х	Z

Z = High Impedance X = Don't Care



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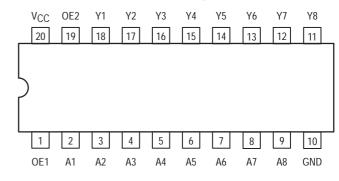
= Assembly Location

= Wafer Lot YY = Year WW = Work Week

ORDERING INFORMATION

Device	Package	Shipping
MC74HC540AN	PDIP-20	1440 / Box
MC74HC540ADW	SOIC-WIDE	38 / Rail
MC74HC540ADWR2	SOIC-WIDE	1000 / Reel

Pinout: 20-Lead Packages (Top View)



MAXIMUM RATINGS*

Symbol	Parameter	Value	Unit
VCC	DC Supply Voltage (Referenced to GND)	- 0.5 to + 7.0	V
V _{in}	DC Input Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
V _{out}	DC Output Voltage (Referenced to GND)	-0.5 to $V_{CC} + 0.5$	V
l _{in}	DC Input Current, per Pin	± 20	mA
l _{out}	DC Output Current, per Pin	± 35	mA
ICC	DC Supply Current, V _{CC} and GND Pins	± 75	mA
PD	Power Dissipation in Still Air Plastic DIP† SOIC Package†	750 500	mW
T _{stg}	Storage Temperature Range	- 65 to + 150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds Plastic DIP or SOIC Package	260	°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND \leq (V_{in} or V_{out}) \leq V_{CC} .

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

SOIC Package: - 7 mW/°C from 65° to 125°C

For high frequency or heavy load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit
VCC	DC Supply Voltage (Referenced to GND)		6.0	V
V _{in} , V _{out}	DC Input Voltage, Output Voltage (Referenced to GND)	0	Vcc	٧
TA	Operating Temperature Range, All Package Types	- 55	+ 125	°C
t _r , t _f	Input Rise/Fall Time $ \begin{array}{c} \text{V}_{CC} = 2.0 \text{ V} \\ \text{(Figure 1)} \end{array} $ $ \begin{array}{c} \text{V}_{CC} = 4.5 \text{ V} \\ \text{V}_{CC} = 6.0 \text{ V} \end{array} $	0 0 0	1000 500 400	ns

DC CHARACTERISTICS (Voltages Referenced to GND)

				V _{CC}	Guaranteed Limit			
Symbol	Parameter	Condit	ion	v	–55 to 25°C	≤85°C	≤125°C	Unit
VIH	Minimum High–Level Input Voltage	$V_{\text{out}} = 0.1V$ $ I_{\text{out}} \le 20\mu\text{A}$		2.0 3.0 4.5 6.0	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	1.50 2.10 3.15 4.20	V
V _{IL}	Maximum Low–Level Input Voltage	$V_{\text{out}} = V_{\text{CC}} - 0.1V$ $ I_{\text{out}} \le 20\mu\text{A}$		2.0 3.0 4.5 6.0	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	0.50 0.90 1.35 1.80	V
VOH	Minimum High–Level Output Voltage	$V_{in} = V_{IL}$ $ I_{Out} \le 20\mu A$		2.0 4.5 6.0	1.9 4.4 5.9	1.9 4.4 5.9	1.9 4.4 5.9	V
		V _{in} = V _{IL}	$\begin{aligned} I_{Out} &\leq 3.6 \text{mA} \\ I_{Out} &\leq 6.0 \text{mA} \\ I_{Out} &\leq 7.8 \text{mA} \end{aligned}$	3.0 4.5 6.0	2.48 3.98 5.48	2.34 3.84 5.34	2.20 3.70 5.20	
VOL	Maximum Low–Level Output Voltage	$V_{in} = V_{IH}$ $ I_{Out} \le 20\mu A$		2.0 4.5 6.0	0.1 0.1 0.1	0.1 0.1 0.1	0.1 0.1 0.1	V
		Vin = VIH	$\begin{aligned} I_{Out} &\leq 3.6 \text{mA} \\ I_{Out} &\leq 6.0 \text{mA} \\ I_{Out} &\leq 7.8 \text{mA} \end{aligned}$	3.0 4.5 6.0	0.26 0.26 0.26	0.33 0.33 0.33	0.40 0.40 0.40	
l _{in}	Maximum Input Leakage Current	$V_{in} = V_{CC}$ or GND		6.0	±0.1	±1.0	±1.0	μА

^{*}Maximum Ratings are those values beyond which damage to the device may occur.

Functional operation should be restricted to the Recommended Operating Conditions.

[†]Derating — Plastic DIP: – 10 mW/°C from 65° to 125°C

DC CHARACTERISTICS (Voltages Referenced to GND)

			vcc	Guara	nteed Lim	iit	
Symbol	Parameter	Condition	V	–55 to 25°C	≤85°C	≤125°C	Unit
loz	Maximum Three–State Leakage Current	Output in High Impedance State V _{in} = V _{IL} or V _{IH} V _{out} = V _{CC} or GND	6.0	±0.5	±5.0	±10.0	μΑ
ICC	Maximum Quiescent Supply Current (per Package)	$V_{in} = V_{CC}$ or GND $I_{out} = 0\mu A$	6.0	4	40	160	μА

NOTE: Information on typical parametric values can be found in Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

AC CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_f = t_f = 6 \text{ ns}$)

			Gu	aranteed Lim	nit	
Symbol	Parameter	V VCC	–55 to 25°C	≤85°C	≤125°C	Unit
^t PLH [,] ^t PHL	Maximum Propagation Delay, Input A to Output Y (Figures 1 and 3)	2.0 3.0 4.5 6.0	80 30 18 15	100 40 23 20	120 55 28 25	ns
^t PLZ [,] ^t PHZ	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
^t PZL [,] ^t PZH	Maximum Propagation Delay, Output Enable to Output Y (Figures 2 and 4)	2.0 3.0 4.5 6.0	110 45 25 21	140 60 31 26	165 75 38 31	ns
t _{TLH} , t _{THL}	Maximum Output Transition Time, Any Output (Figures 1 and 3)	2.0 3.0 4.5 6.0	60 22 12 10	75 28 15 13	90 34 18 15	ns
C _{in}	Maximum Input Capacitance		10	10	10	pF
C _{out}	Maximum Three—State Output Capacitance (Output in High Impedance State)		15	15	15	pF

NOTE: For propagation delays with loads other than 50 pF, and information on typical parametric values, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

		Typical @ 25°C, $V_{CC} = 5.0 \text{ V}$, $V_{EE} = 0 \text{ V}$	
C _{PD}	Power Dissipation Capacitance (Per Buffer)*	35	pF

^{*} Used to determine the no-load dynamic power consumption: PD = CPD VCC²f + ICC VCC. For load considerations, see Chapter 2 of the ON Semiconductor High-Speed CMOS Data Book (DL129/D).

SWITCHING WAVEFORMS

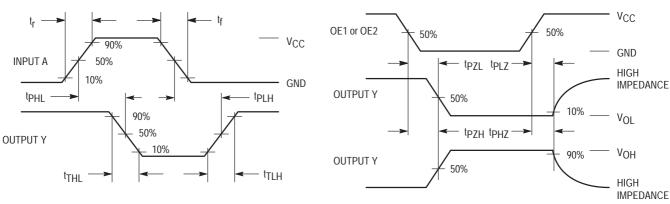
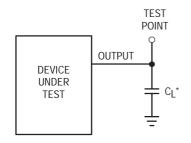


Figure 1. Figure 2.

TEST CIRCUITS



 $\begin{array}{c|c} & \text{POINT} \\ \hline \text{DEVICE} \\ \text{UNDER} \\ \text{TEST} \end{array} \begin{array}{c} \text{OUTPUT} & \begin{array}{c} \text{Ik}\Omega \\ \\ \text{Ik}\Omega \end{array} \end{array} \begin{array}{c} \text{CONNECT TO V}_{CC} \text{ WHEN} \\ \text{TESTING tp}_{LZ} \text{ AND tp}_{ZL}. \\ \text{CONNECT TO GND WHEN} \\ \text{TESTING tp}_{HZ} \text{ and tp}_{ZH}. \end{array}$

TEST

*Includes all probe and jig capacitance

*Includes all probe and jig capacitance

Figure 3.

Figure 4.

PIN DESCRIPTIONS

INPUTS

A1, A2, A3, A4, A5, A6, A7, A8 (PINS 2, 3, 4, 5, 6, 7, 8,

9) — Data input pins. Data on these pins appear in inverted form on the corresponding Y outputs, when the outputs are enabled.

CONTROLS

OE1, OE2 (PINS 1, 19) — Output enables (active-low). When a low voltage is applied to both of these pins, the

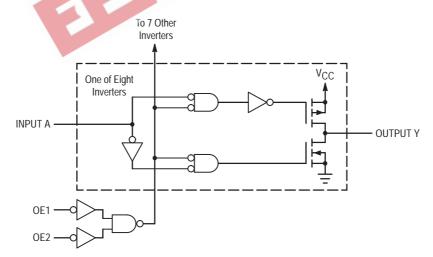
outputs are enabled and the device functions as an inverter. When a hgih voltage is applied to either input, the outputs assume the high impedance state.

OUTPUTS

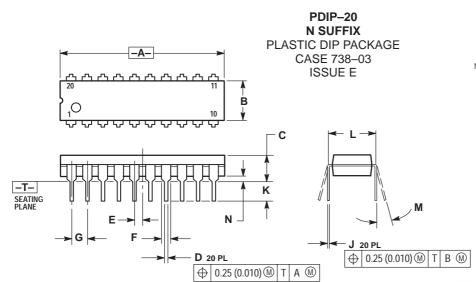
Y1, Y2, Y3, Y4, Y5, Y6, Y7, Y8 (PINS 18, 17, 16, 15, 14,

13, 12, 11) — Device outputs. Depending upon the state of the output enable pins, these outputs are either inverting outputs or high-impedance outputs.

LOGIC DETAIL



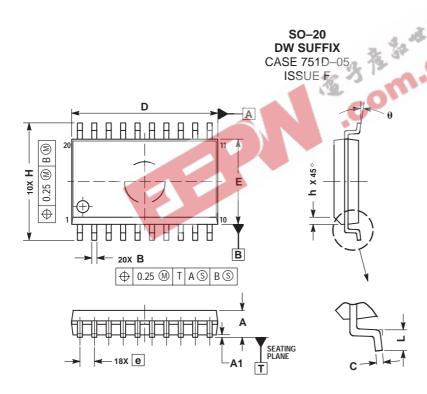
PACKAGE DIMENSIONS



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI
- TO DIMENSIONING AND TOLERANGING PER AL Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
 DIMENSION L TO CENTER OF LEAD WHEN FORMED PARALLEL.
- 4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.

	INCHES		MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	1.010	1.070	25.66	27.17	
В	0.240	0.260	6.10	6.60	
С	0.150	0.180	3.81	4.57	
D	0.015	0.022	0.39	0.55	
Ε	0.050 BSC		1.27 BSC		
F	0.050	0.070	1.27	1.77	
G	0.100	BSC	2.54 BSC		
J	0.008	0.015	0.21	0.38	
K	0.110	0.140	2.80	3.55	
L	0.300 BSC		7.62	BSC	
M	0 °	15°	0°	15°	
N	0.020	0.040	0.51	1.01	

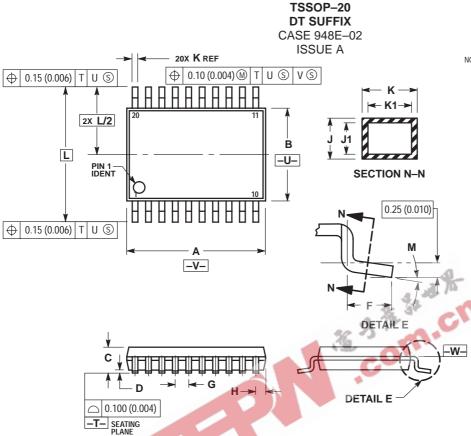


- NOTES:
 1. DIMENSIONS ARE IN MILLIMETERS.
 2. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 1994.
 3. DIMENSIONS D AND E DO NOT INCLUDE MOLD PROTRUSION.
 4. MAXIMUM MOLD PROTRUSION 0.15 PER SIDE.

 - DIMENSION B DOES NOT INCLUDE DAMBAR
 PROTRUSION. ALLOWABLE PROTRUSION SHALL
 BE 0.13 TOTAL IN EXCESS OF B DIMENSION AT
 MAXIMUM MATERIAL CONDITION.

	MILLIMETERS			
DIM	MIN	MAX		
Α	2.35	2.65		
A1	0.10	0.25		
В	0.35	0.49		
С	0.23	0.32		
D	12.65	12.95		
Е	7.40	7.60		
е	1.27	BSC		
Н	10.05	10.55		
h	0.25	0.75		
L	0.50	0.90		
θ	0°	7 °		

PACKAGE DIMENSIONS



- NOTES:

 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: MILLIMETER.
 3. DIMENSION A DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH OR GATE BURRS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
 4. DIMENSION B DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION. INTERLEAD FLASH OR PROTRUSION SHALL NOT EXCEED 0.25 (0.010) PER SIDE.
 5. DIMENSION K DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE K DIMENSION AT MAXIMUM MATERIAL CONDITION.
 6. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
 7. DIMENSION A AND B ARE TO BE DETERMINED AT DATUM PLANE W...

	MILLIMETERS		INC	HES	
DIM	MIN	MAX	MIN	MAX	
Α	6.40	6.60	0.252	0.260	
В	4.30	4.50	0.169	0.177	
С		1.20		0.047	
D	0.05	0.15	0.002	0.006	
F	0.50	0.75	0.020	0.030	
G	0.65	BSC	0.026 BSC		
Н	0.27	0.37	0.011	0.015	
J	0.09	0.20	0.004	0.008	
J1	0.09	0.16	0.004	0.006	
K	0.19	0.30	0.007	0.012	
K1	0.19	0.25	0.007	0.010	
L	6.40	BSC	0.252 BSC		
М	0°	8°	0 °	8°	

Notes





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